

N-CHANNEL SILICON POWER MOSFET

FAP-2S Series

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

(Tc=25°C unless otherwise specified)

| Item | Symbol | Ratings | Unit |
|---|-------------------------------------|---------------------|------|
| Drain-source voltage | V _{DS} | 500 | V |
| Continuous drain current | I _D | ±6 | A |
| Pulsed drain current | I _{D(puls)} | ±24 | A |
| Gate-source voltage | V _{GS} | ±35 | V |
| Repetitive or non-repetitive | IAR*2 | 6 | A |
| Maximum Avalanche Energy | EAS*1 | 259.1 | mJ |
| Max. power dissipation | P _D | 50 | W |
| Operating and storage temperature range | T _{ch} T _{stg} | +150 -55 to +150 | °C |

*1 L=13.2mH, V_{CC}=50V *2 T_{ch}≥150°C

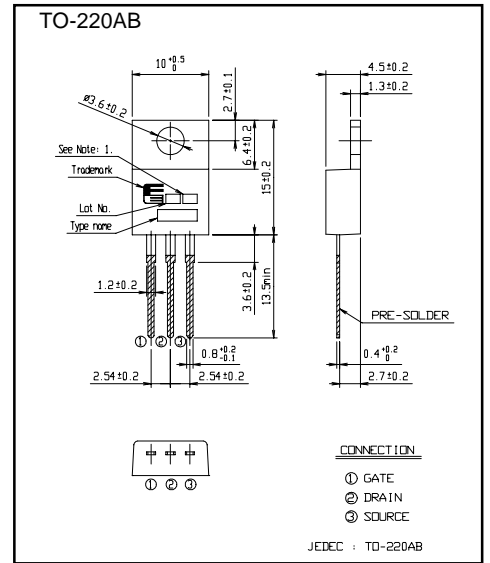
Electrical characteristics (Tc =25°C unless otherwise specified)

| Item | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|----------------------------------|----------------------|--|------|------|------|-------|
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D =1mA V _{GS} =0V | 500 | | | V |
| Gate threshold voltage | V _{GS(th)} | I _D =1mA V _{DS} =V _{GS} | 3.5 | 4.0 | 4.5 | V |
| Zero gate voltage drain current | I _{DSS} | V _{DS} =500V V _{GS} =0V | | 10 | 500 | μA |
| | | | | 0.2 | 1.0 | mA |
| Gate-source leakage current | I _{GSS} | V _{GS} =±35V V _{DS} =0V | | 10 | 100 | nA |
| Drain-source on-state resistance | R _{DS(on)} | I _D =3A V _{GS} =10V | | 1.25 | 1.5 | Ω |
| Forward transconductance | g _{fs} | I _D =3A V _{DS} =25V | 2 | 4 | | S |
| Input capacitance | C _{iss} | V _{DS} =25V | | 540 | 810 | pF |
| Output capacitance | C _{oss} | V _{GS} =0V | | 100 | 150 | |
| Reverse transfer capacitance | C _{rss} | f=1MHz | | 45 | 70 | ns |
| Turn-on time t _{on} | t _{d(on)} | V _{CC} =300V I _D =6A | | 13 | 20 | |
| | t _r | V _{GS} =10V | | 30 | 45 | |
| Turn-off time t _{off} | t _{d(off)} | R _{GS} =10Ω | | 40 | 60 | |
| | t _f | | | 25 | 40 | |
| Avalanche capability | I _{AV} | L=13.2 mH T _{ch} =25°C | 6 | | | A |
| Diode forward on-voltage | V _{SD} | I _F =2I _{DR} V _{GS} =0V T _{ch} =25°C | | 1.0 | 1.5 | V |
| Reverse recovery time | t _{rr} | I _F =I _{DR} V _{GS} =0V | | 450 | | ns |
| Reverse recovery charge | Q _{rr} | -di/dt=100A/μs T _{ch} =25°C | | 3.2 | | μC |

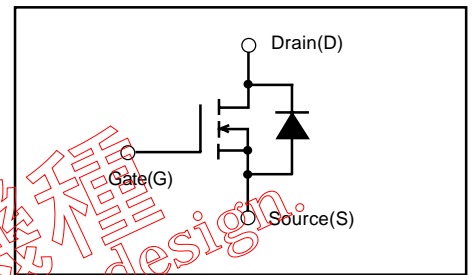
Thermal characteristics

| Item | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------|-----------------------|--------------------|------|------|------|-------|
| Thermal resistance | R _{th(ch-c)} | channel to case | | | 2.50 | °C/W |
| | R _{th(ch-a)} | channel to ambient | | | 75.0 | °C/W |

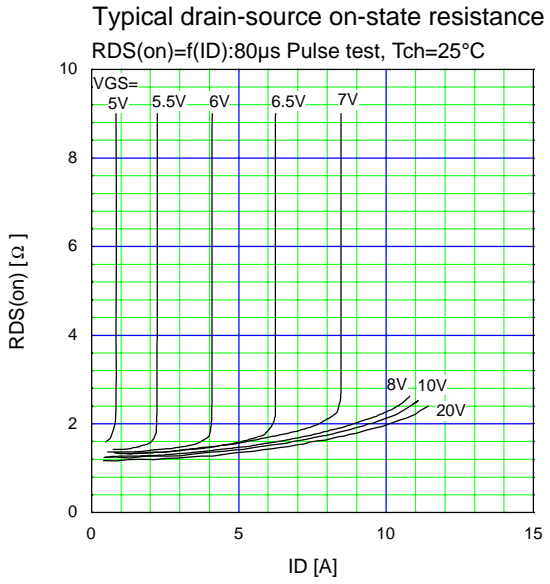
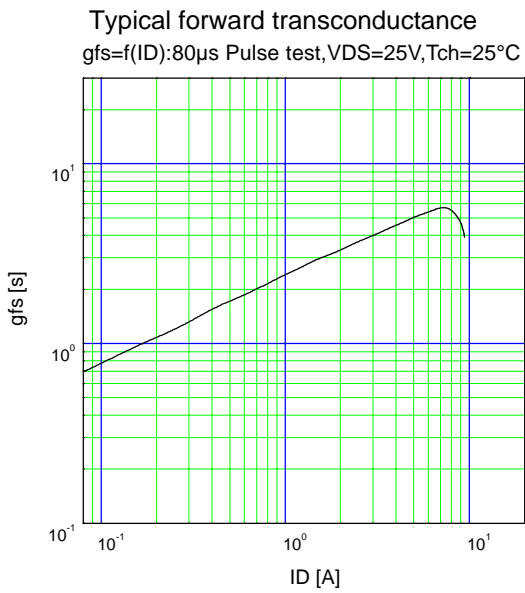
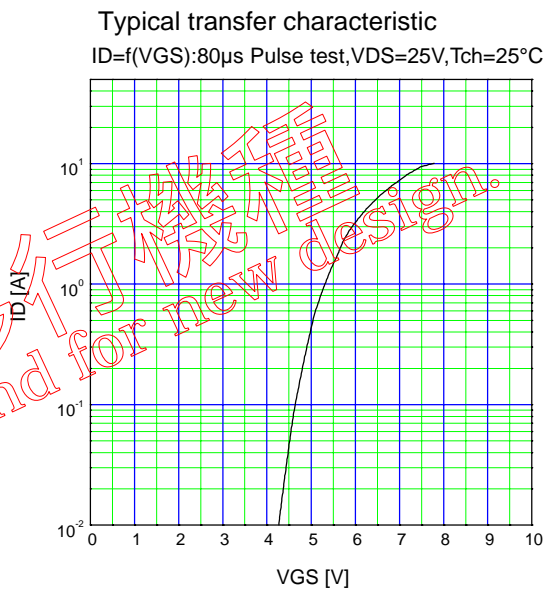
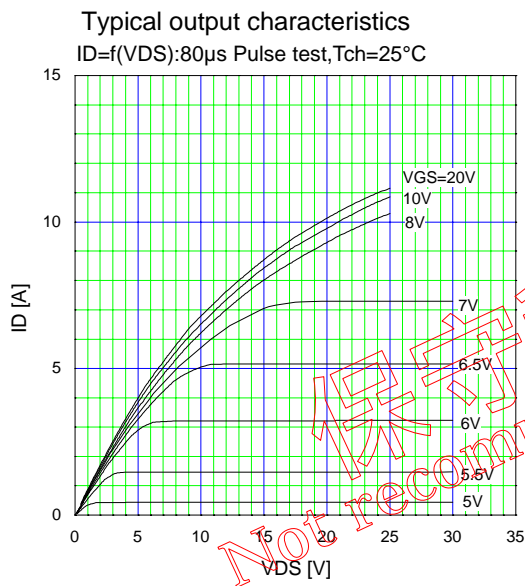
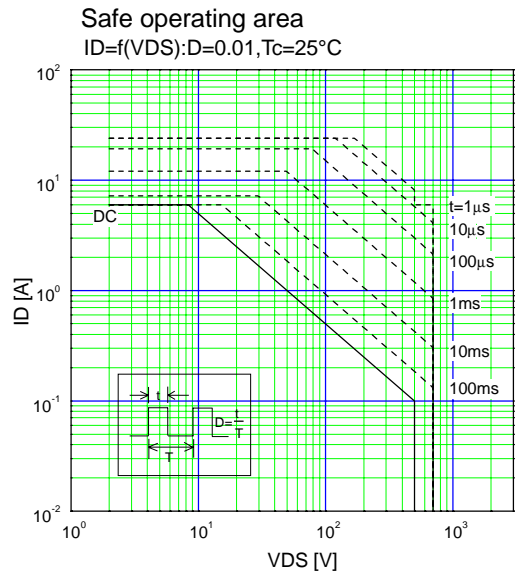
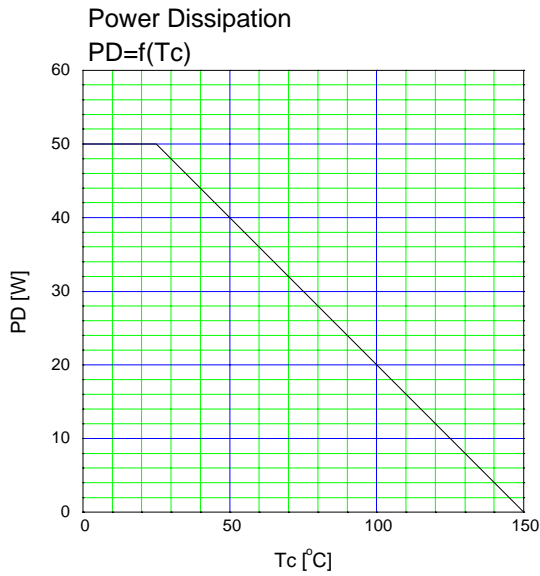
Outline Drawings



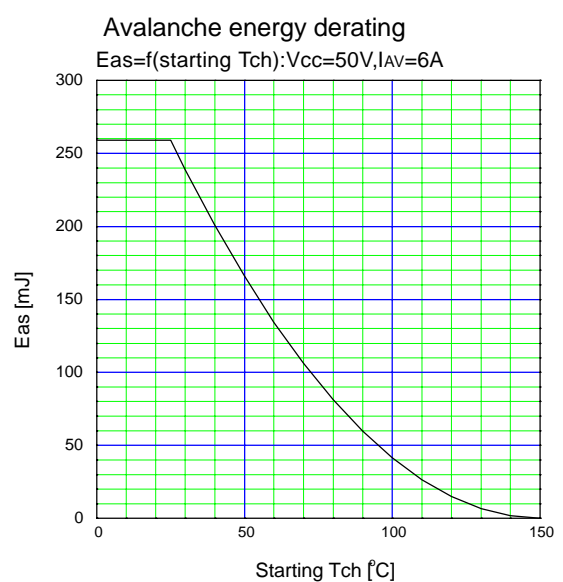
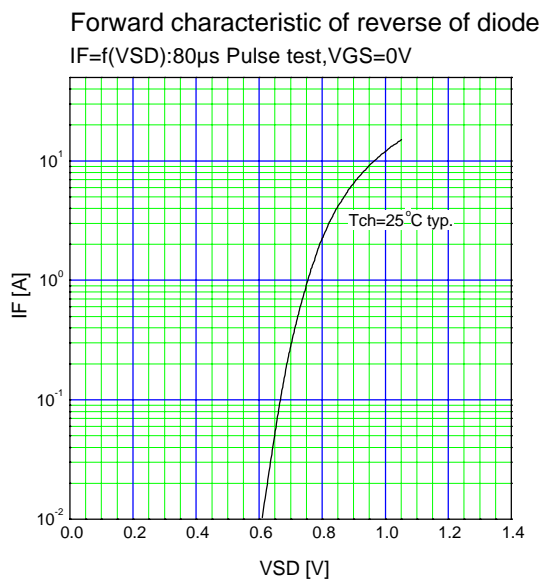
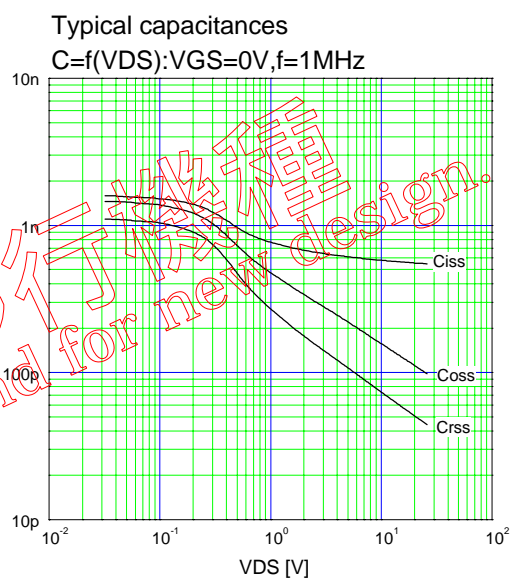
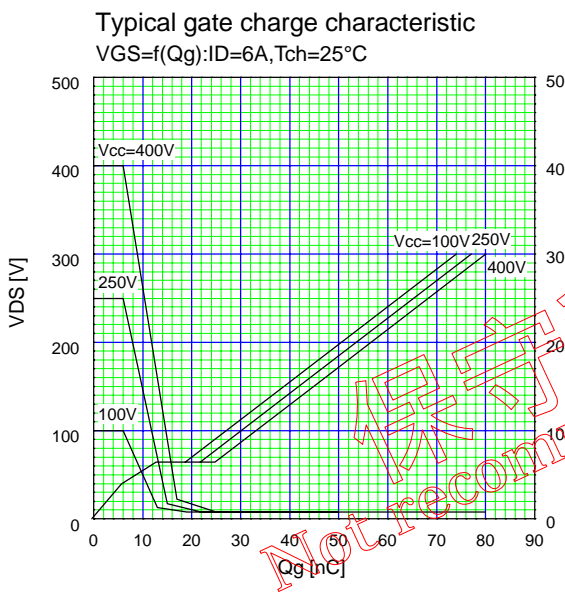
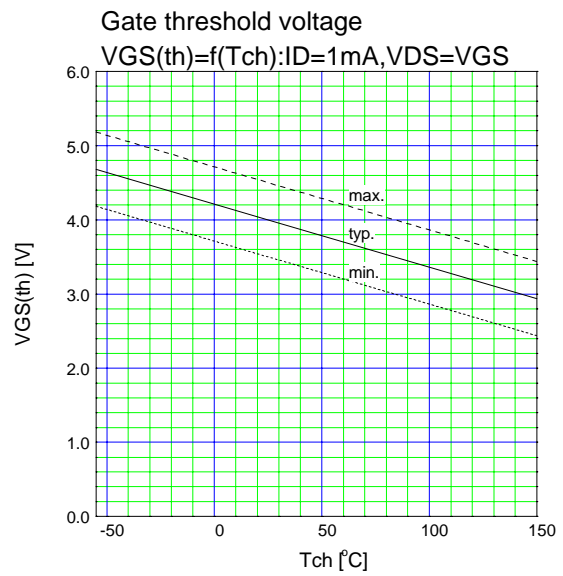
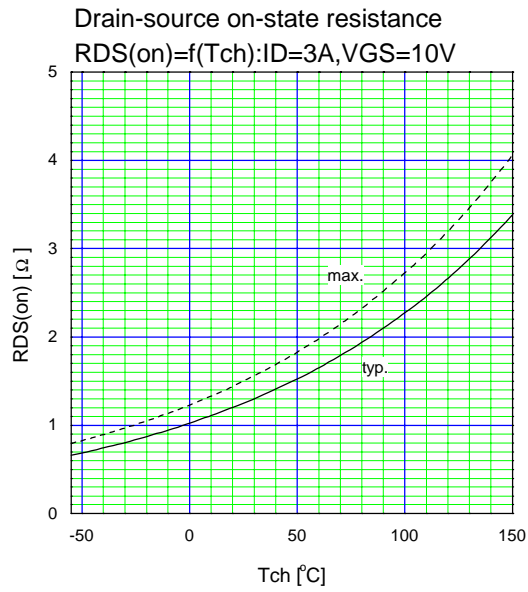
Equivalent circuit schematic

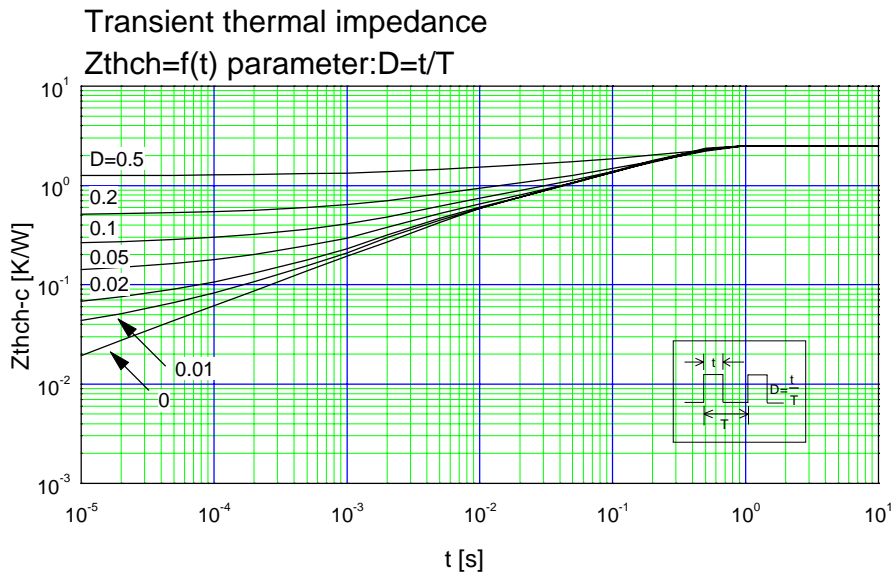


Characteristics



不建议移打此器件
 Not recommend for new design.





保守移行機種
Not recommend for new design.